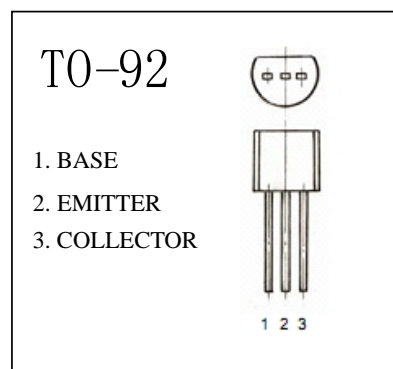




KSP10 TRANSISTOR(NPN)

MAXIMUM RATINGS(Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
VCBO	Collector-Base Voltage	30	V
VCEO	Collector-Emitter Voltage	25	V
VEBO	Emitter-Base Voltage	3	V
IC	Collector Current	0.05	A
PC	Collector Power Dissipation	350	mW
Tj	Junction Temperature	150	°C
Tstg	Storage Temperature	-55~150	°C



ELECTRICAL CHARACTERISTICS(Tamb=25°C unless otherwise specified):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR)CBO	Ic=100uA, Ib=0	30			V
Collector-emitter breakdown voltage	V(BR)CEO	Ic=1mA, IE=0	25			V
Emitter-base breakdown voltage	V(BR)EBO	Ic=100uA, Ic=0	3			V
Collector cut-off current	ICBO	VCB=30V, IE=0			0.5	μA
Emitter cut-off current	IEBO	VEB=3V, Ic=0			0.1	μA
DC current gain	HFE	Vce=10V, Ic=4mA	60		200	
Collector-emitter saturation voltage	VCE(sat)	Ic=4mA, Ib=0.4mA			0.5	V
Base-emitter saturation voltage	VBE(sat)	Ic=4mA, Ib=0.4mA			0.95	V
Gain Bandwidth Product	fT	VCE=10V, Ic=4mA, f=100MHz	650			MHz
Output Capacitance	Cob	VCB=10V, IE=0, f=1MHz			0.7	pF